



STB11NK40Z, STP11NK40ZFP STP11NK40Z

N-channel 400 V, 0.49 Ω , 9 A, TO-220, TO-220FP, D²PAK
Zener-protected SuperMESH™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STB11NK40Z	400V	<0.55 Ω	10A	110W
STP11NK40Z	400V	<0.55 Ω	10A	110W
STP11NK40ZFP	400V	<0.55 Ω	10A	30W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

Applications

- Switching application

Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications.

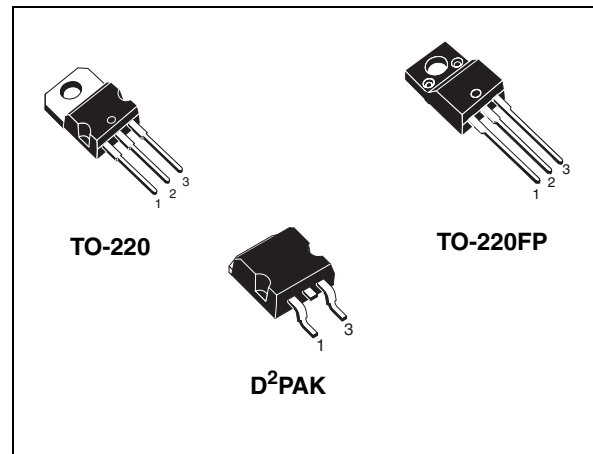


Figure 1. Internal schematic diagram

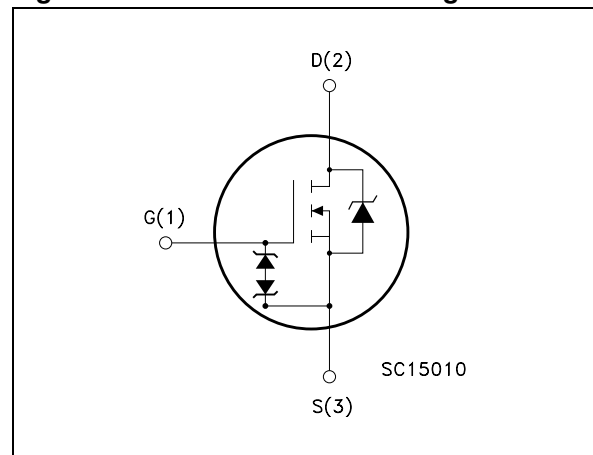


Table 1. Device summary

Order code	Marking	Package	Packaging
STB11NK40ZT4	B11NK40Z	D ² PAK	Tape and reel
STP11NK40Z	P11NK40Z	TO-220	Tube
STP11NK40ZFP	P11NK40ZFP	TO-220FP	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220/D ² PAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	400		V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20k\Omega$)	400		V
V_{GS}	Gate-source voltage	± 30		V
I_D	Drain current (continuous) at $T_C = 25^\circ C$	9	$9^{(1)}$	A
I_D	Drain current (continuous) at $T_C = 100^\circ C$	5.67	$5.67^{(1)}$	A
$I_{DM}^{(2)}$	Drain current (pulsed)	36	$36^{(1)}$	A
P_{TOT}	Total dissipation at $T_C = 25^\circ C$	110	30	W
	Derating factor	0.88	0.24	W/ $^\circ C$
$V_{ESD(G-S)}$	Gate source ESD (HBM-C= 100pF, R= 1.5k Ω)	3500		V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5		V/ns
V_{ISO}	Insulation withstand voltage (DC)	--	2500	V
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150		$^\circ C$

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 9A$, $di/dt \leq 200 A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq T_{JMAX}$.

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-220/D ² PAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.14	4.2	$^\circ C/W$
R_{thj-a}	Thermal resistance junction-ambient max	62.5		$^\circ C/W$
T_I	Maximum lead temperature for soldering purpose	300		$^\circ C$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	9	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25^{\circ}\text{C}$, $I_d=I_{AR}$, $V_{DD}=50\text{V}$)	190	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$, $V_{GS} = 0$	400			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating @ } 125^{\circ}\text{C}$			1 50	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 4.5\text{A}$		0.49	0.55	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$, $I_D = 4.5\text{A}$	-	5.8	-	S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{MHz}$, $V_{GS} = 0$	-	930 140 30	-	pF pF pF
$C_{oss\ eq}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{V to } 320\text{V}$	-	78	-	pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 320\text{V}$, $I_D = 9\text{A}$ $V_{GS} = 10\text{V}$ (see Figure 18)	-	32 6 18.5	-	nC nC nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $C_{oss\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD}=200\text{ V}$, $I_D=4.5\text{ A}$, $R_G=4.7\Omega$, $V_{GS}=10\text{ V}$ (see Figure 20)	-	20 20	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD}=200\text{ V}$, $I_D=4.5\text{ A}$, $R_G=4.7\Omega$, $V_{GS}=10\text{ V}$ (see Figure 20)	-	40 18	-	ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage rise time Fall time Cross-over time	$V_{DD}=320\text{ V}$, $I_D=9\text{ A}$, $R_G=4.7\Omega$, $V_{GS}=10\text{ V}$ (see Figure 20)	-	15 17 30	-	ns ns ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		36	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=9\text{ A}$, $V_{GS}=0$	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}=45\text{ V}$, $T_J=150^\circ\text{C}$	-	225 1.6 14		ns μC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5 %

Table 9. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{GS}=\pm 1\text{ mA}$ (open drain)	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 D²PAK

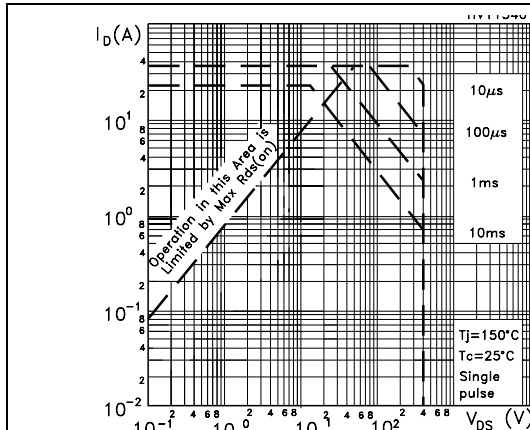


Figure 3. Thermal impedance for TO-220 D²PAK

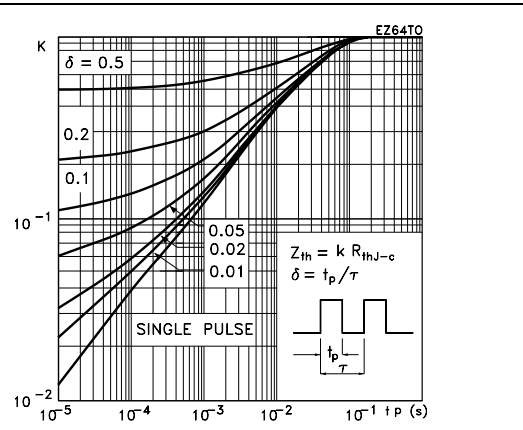


Figure 4. Safe operating area for TO-220FP

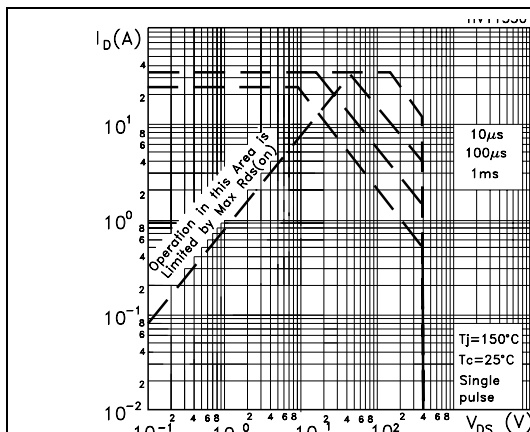


Figure 5. Thermal impedance for TO-220FP

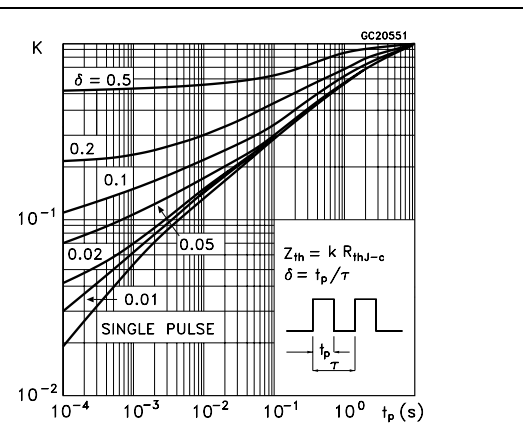


Figure 6. Output characteristics

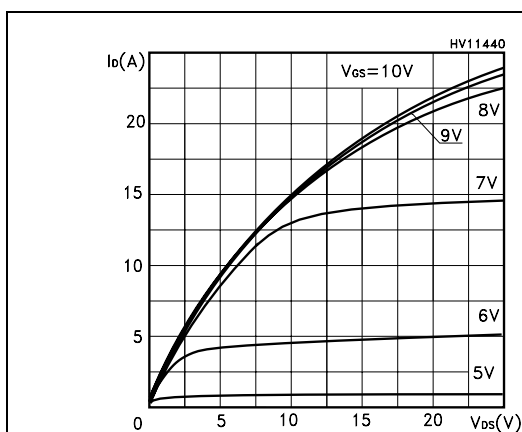


Figure 7. Transfer characteristics

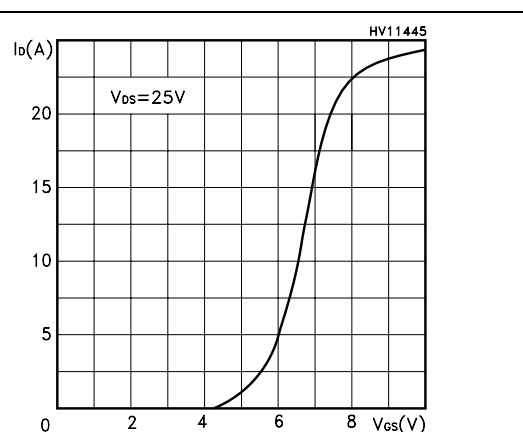


Figure 8. Transconductance

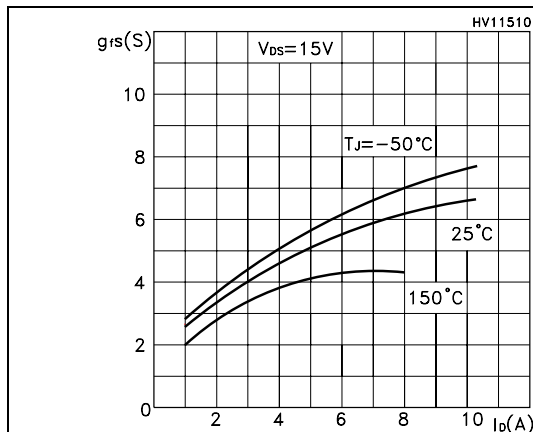


Figure 9. Static drain-source on resistance

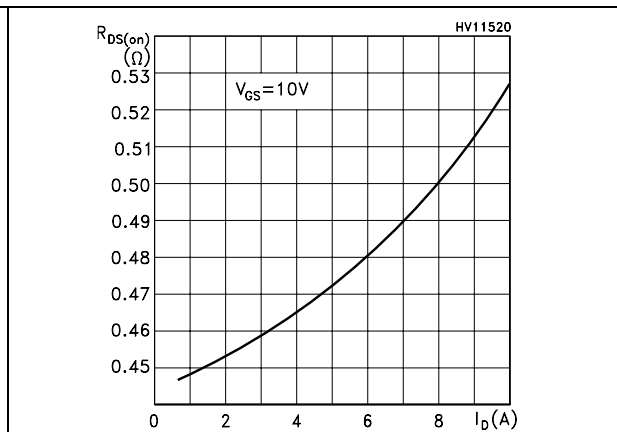


Figure 10. Gate charge vs gate-source voltage

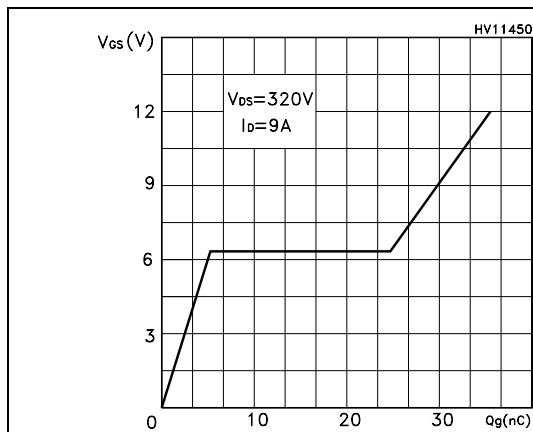


Figure 11. Capacitance variations

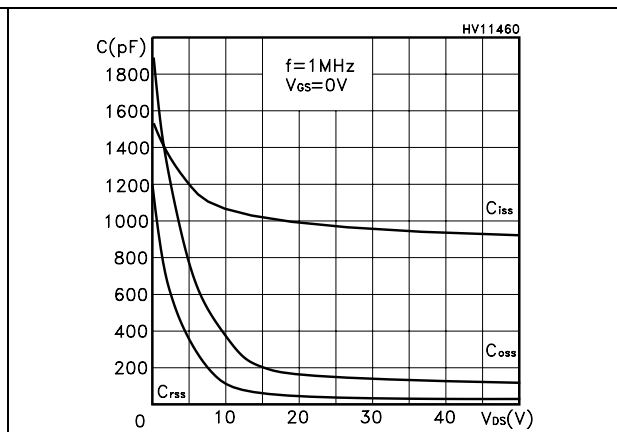


Figure 12. Normalized gate threshold voltage vs temperature

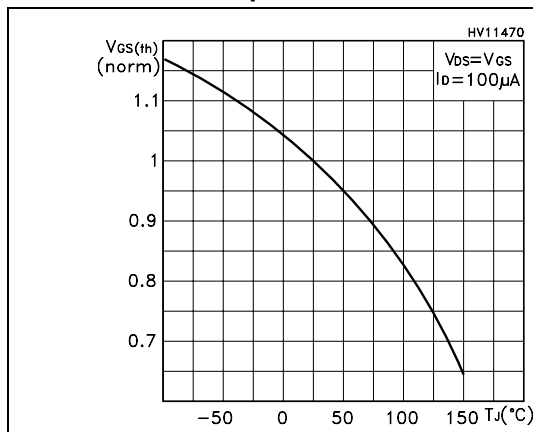


Figure 13. Normalized on resistance vs temperature

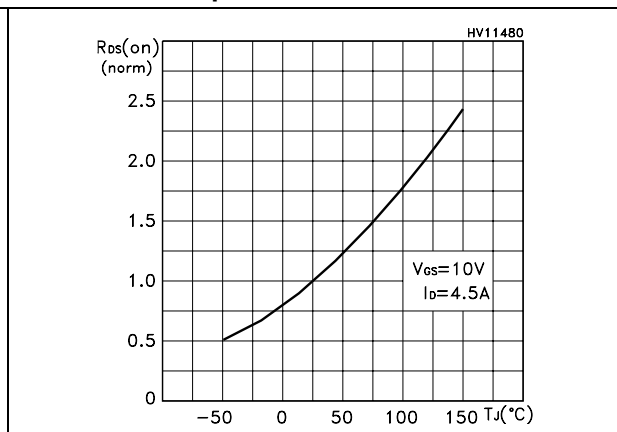


Figure 14. Source-drain diode forward characteristics

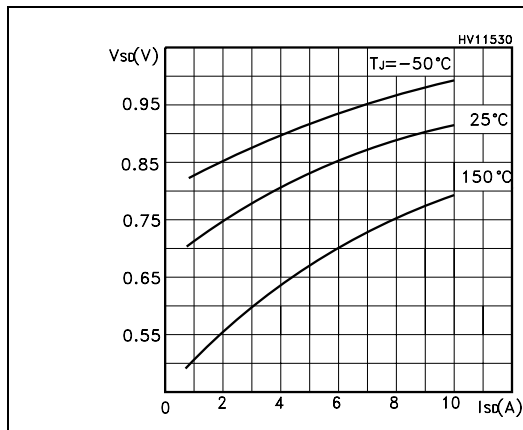


Figure 15. Normalized $B_{V_{DSS}}$ vs temperature

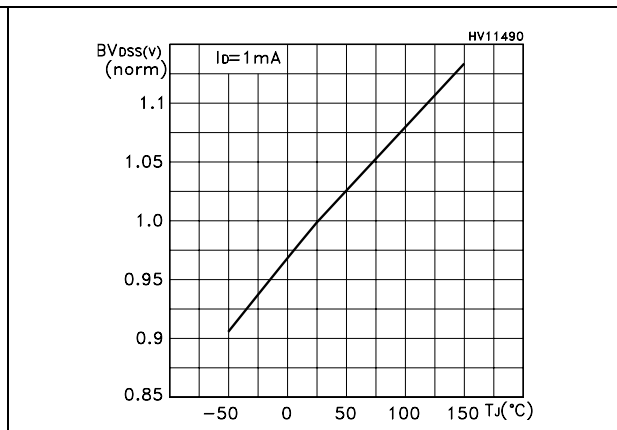
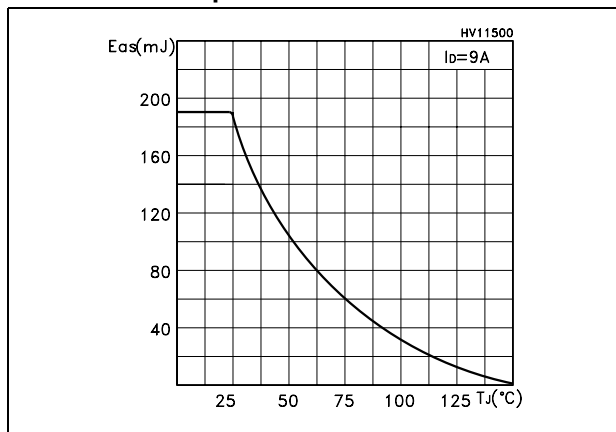


Figure 16. Maximum avalanche energy vs temperature



3 Test circuits

Figure 17. Switching times test circuit for resistive load

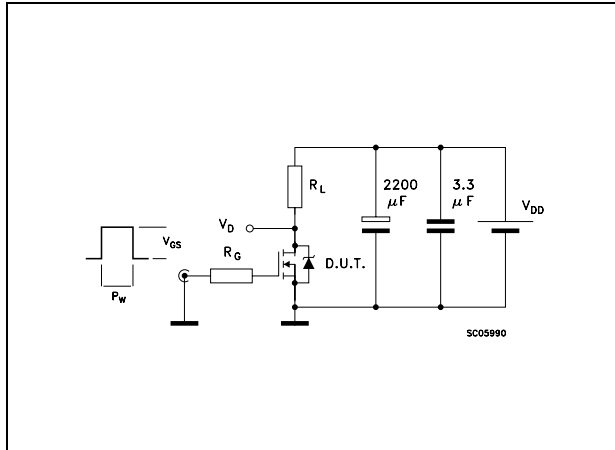


Figure 18. Gate charge test circuit

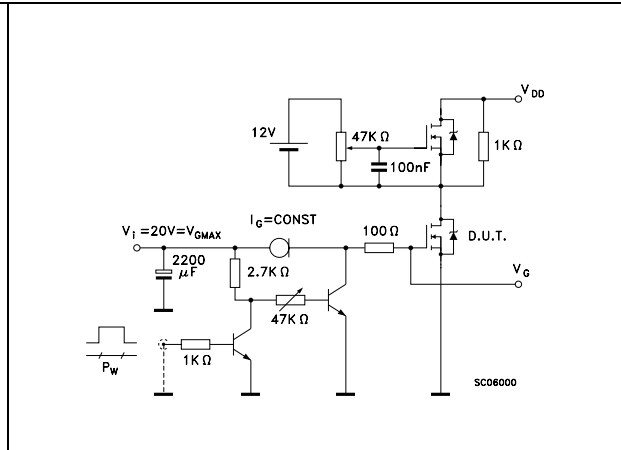


Figure 19. Test circuit for inductive load switching and diode recovery times

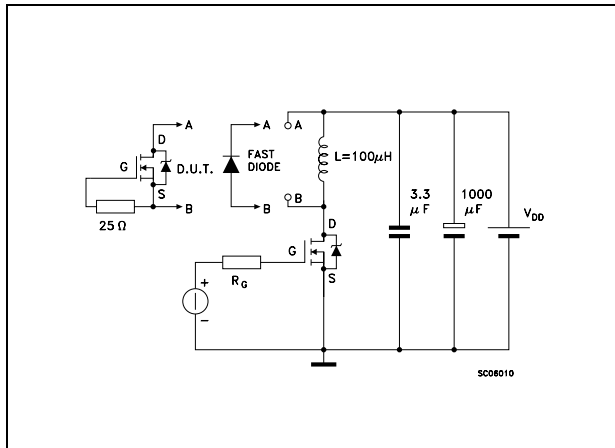


Figure 20. Unclamped inductive load test circuit

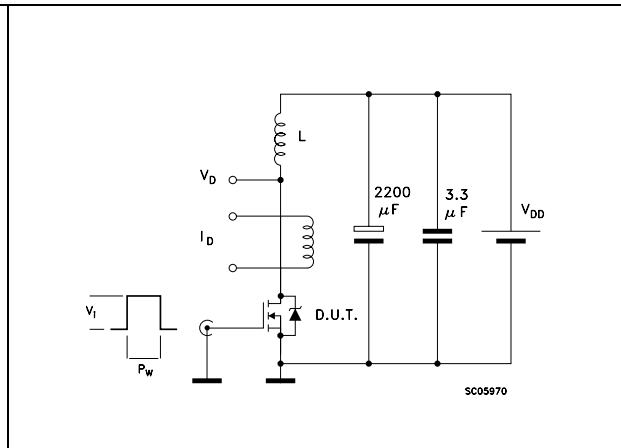


Figure 21. Unclamped inductive waveform

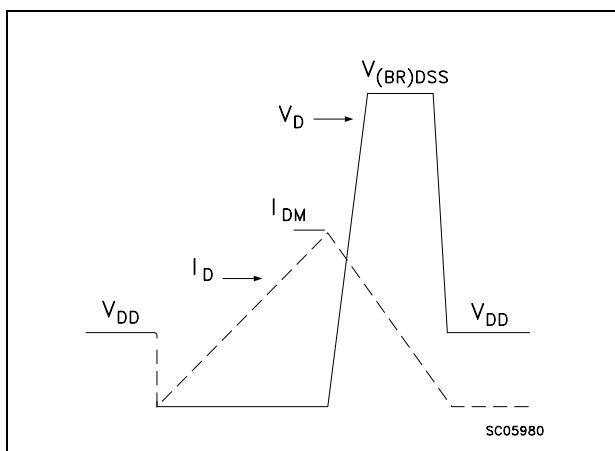
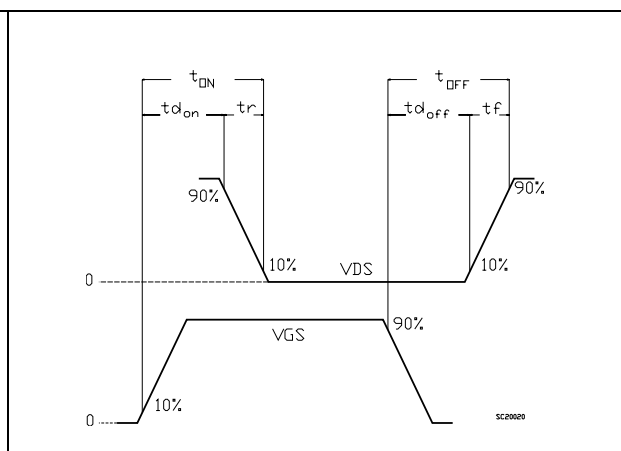


Figure 22. Switching time waveform

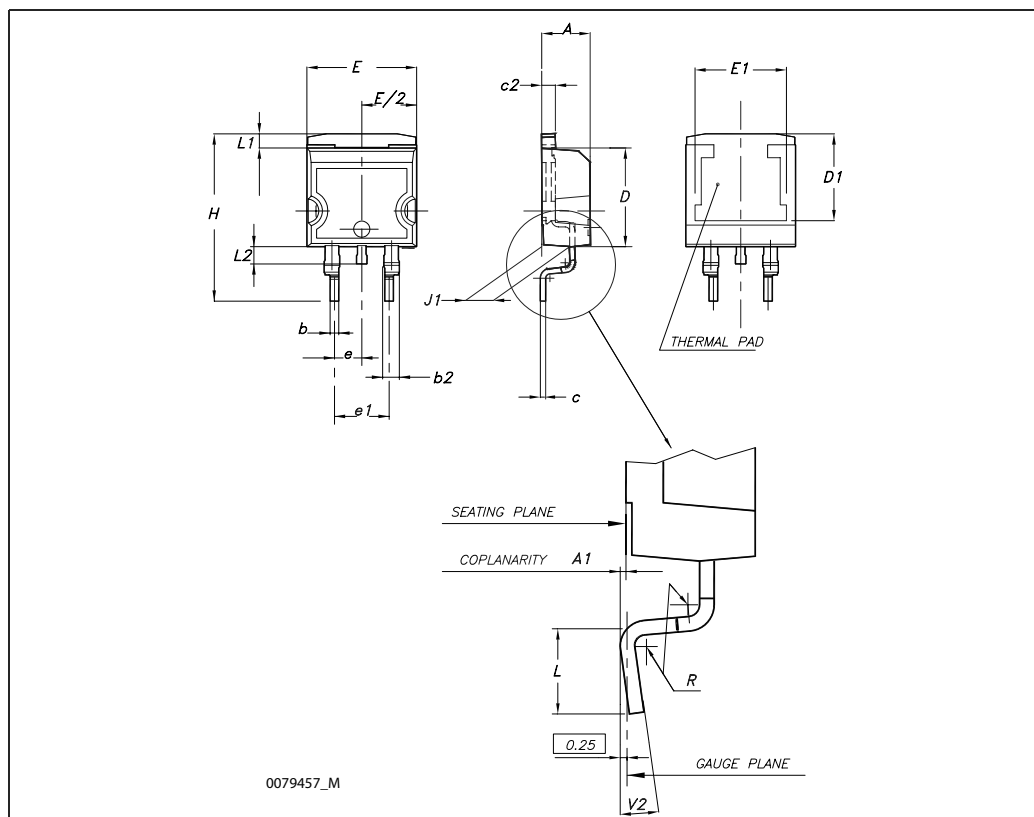


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

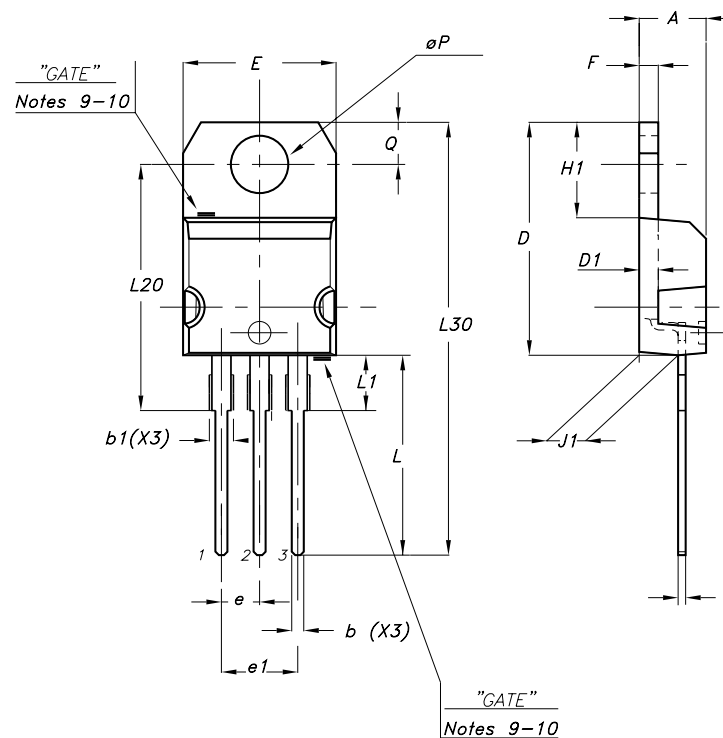
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



TO-220 mechanical data

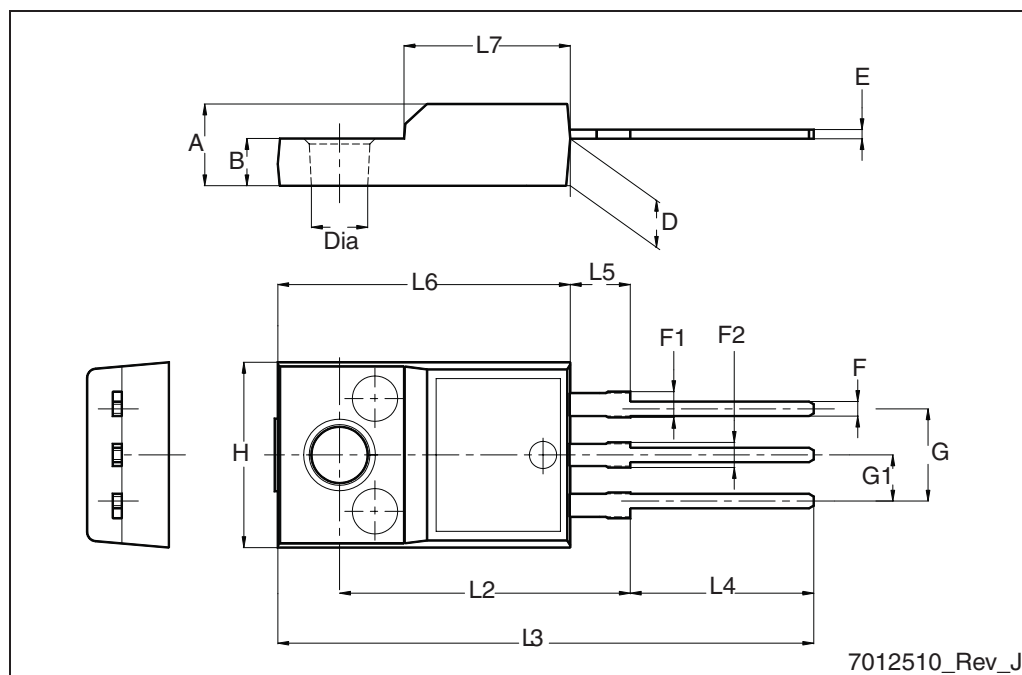
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



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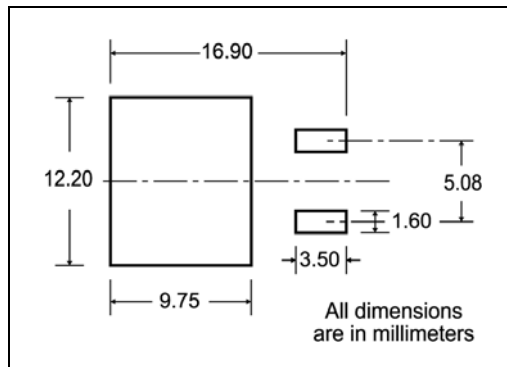
TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

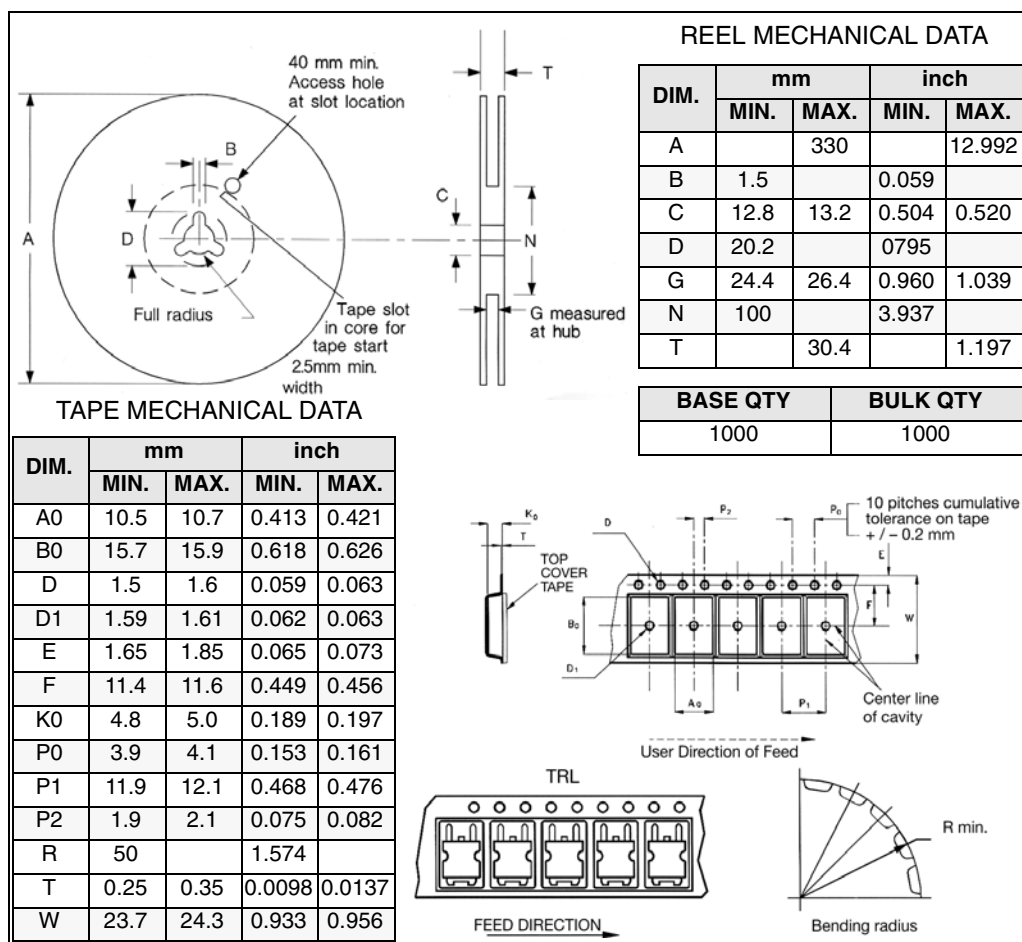


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 10. Document revision history

Date	Revision	Changes
23-Aug-2005	2	Preliminary version
28-Oct-2005	3	Complete version
26-Jul-2006	4	New template, no content change
22-Nov-2006	5	Corrected unit on Table 5.: On/off states
18-Jan-2007	6	Typo mistakes on page 1
20-Apr-2009	7	Updated mechanical data

STB11NK40Z, STP11NK40ZFP, STP11NK40Z

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